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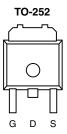
N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
100	0.095 at $V_{GS} = 10 \text{ V}$	15		
100	0.100 at V _{GS} = 6 V	15		

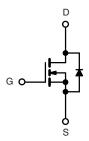
FEATURES

- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R_g Tested





Top View



N-Channel MOSFET

APPLICATIONS

• Primary Side Switch

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	100				
Gate-Source Voltage			± 20	V		
Continuous Drain Current /T 175 °C\b	T _C = 25 °C	L	15			
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 125 °C	l _D	8.7	ı		
Pulsed Drain Current	I _{DM}	25	Α			
Continuous Source Current (Diode Conduction)	I _S	15				
Avalanche Current	I _{AR}	15				
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	11.3	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D	62 ^b	W		
Maximum Fower Dissipation	T _A = 25 °C	' D	2.7 ^a			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	16	20	°C/W	
Junction-to-Ambient*	Steady State		45	55		
Junction-to-Case		R _{thJC}	2	2.4		

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2				
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V			1) μΑ	
Zero Gate Voltage Drain Current		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	15			Α	
		V _{GS} = 10 V, I _D = 15 A		0.077	0.095		
5 h	В	V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C			0.190		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C			0.250	Ω	
		V _{GS} = 6 V, I _D = 10 A		0.081	0.100		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		25		S	
Dynamic ^a							
Input Capacitance	C _{iss}			900		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		115			
Reverse Transfer Capacitance	C _{rss}			70			
Total Gate Charge ^c	Q_g			20	25		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$		5.5		nC	
Gate-Drain Charge ^c	Q_{gd}			7		1	
Gate Resistance	R_g		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			8	12		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		35	55	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		17	25		
Fall Time ^c	t _f			30	45		
Source-Drain Diode Ratings and Characteristic (T _C = 25 °C)							
Pulsed Current	I _{SM}				15	Α	
Diode Forward Voltage ^b	V_{SD}	$I_F = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 15 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		55	85	ns	

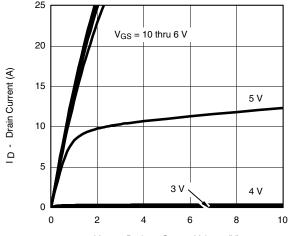
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

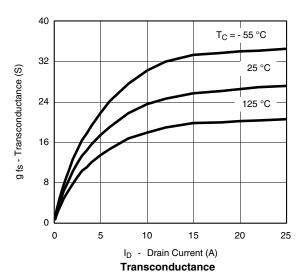
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)

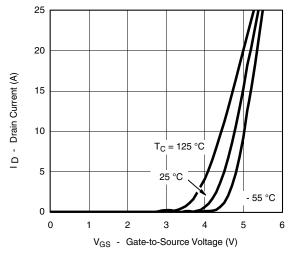


 V_{DS} - Drain-to-Source Voltage (V) **Output Characteristics**

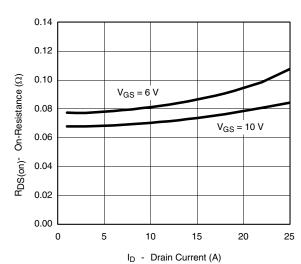


1500 1200 1200 900 600 300 C_{rss} C_{oss} 0 0 20 40 60 80 100

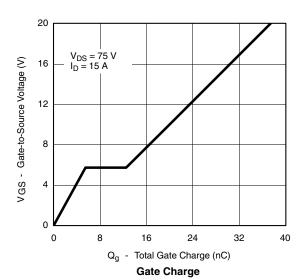
V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



Transfer Characteristics

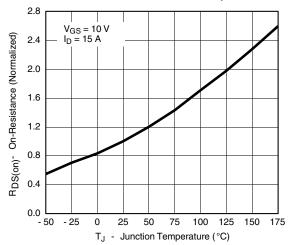


On-Resistance vs. Drain Current



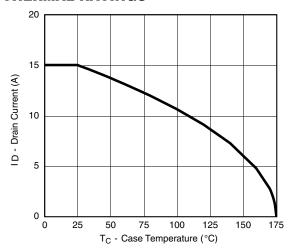


TYPICAL CHARACTERISTICS (25 °C unless noted)

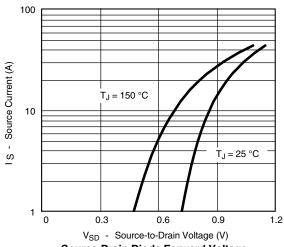


On-Resistance vs. Junction Temperature

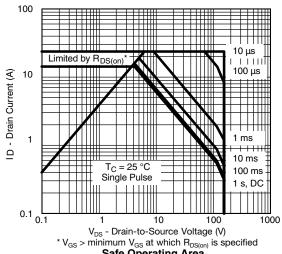
THERMAL RATINGS



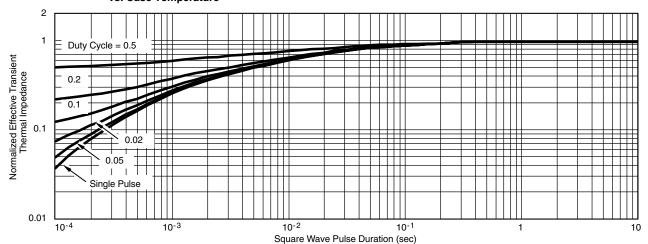
Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



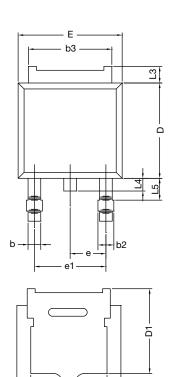
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified **Safe Operating Area**



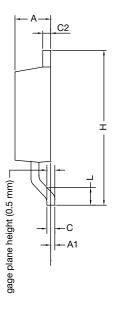
Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE



E1



	MILLIMETERS		INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
А	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC 0.090 BSC		2.28 BSC		BSC
e1	4.56 BSC		0.180	BSC		
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12-0247-Rev. M, 24-Dec-12						

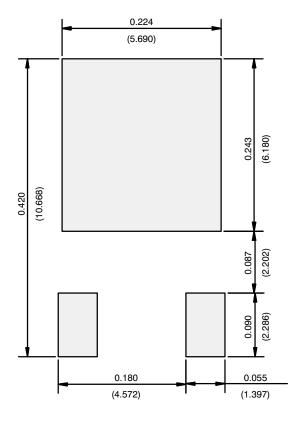
DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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